UNISONIC TECHNOLOGIES CO., LTD

RB520S30

DIODE

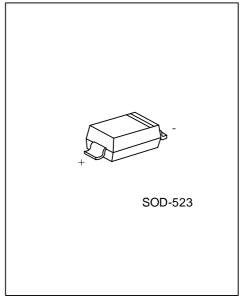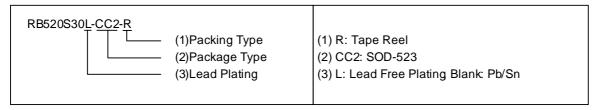## SCHOTTKY BARRIER DIODE

■ **FEATURES**

* Miniature surface mounting type
* Low forward voltage drop (V_F=0.50V Typ. at 200mA)
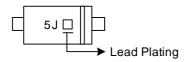* Low reverse leakage current (I_R=0.1uA Typ. at 10V)
* Fast switching speed

SOD-523

*Pb-free plating product number: RB520S30L

■ **ORDERING INFORMATION**

Order Number		Package	Packing
Normal	Lead Free Plating		
RB520S30-CC2-R	RB520S30L-CC2-R	SOD-523	Tape Reel

RB520S30L-CC2-R

(1) Packing Type
(2) Package Type
(3) Lead Plating

(1) R: Tape Reel
(2) CC2: SOD-523
(3) L: Lead Free Plating Blank: Pb/Sn

■ **MARKING**

5J

Lead Plating

QW-R601-011,A

RB520S30

DIODE

■ **ABSOLUTE MAXIMUM RATINGS** (Single Diode @T_A=25)

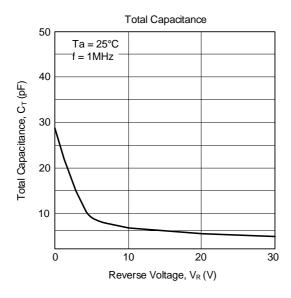| PARAMETER	SYMBOL	RATINGS	UNIT
Maximum Reverse Voltage (DC)	V_R	30	V
Average Rectified Forward Current	I_{OUT}	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1	A
Junction Temperature	T_J	+125	
Storage Temperature	T_{STG}	-40 ~ +125	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.
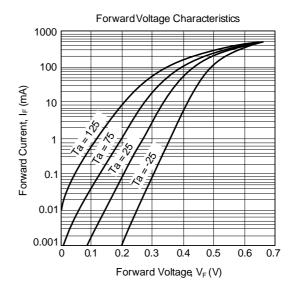
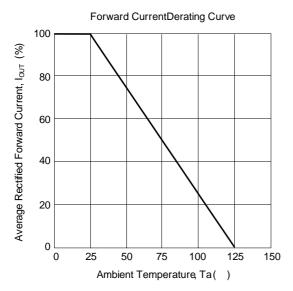■ **ELECTRICAL CHARACTERISTICS** (T_A=25 , unless otherwise specified)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage Drop	V_F	I_F=200mA			0.6	V
Reverse Leakage Current	I_R	V_R=10V			1	µA

■ **TYPICAL CHARACTERISTICS**

Total Capacitance

Ta = 25°C
f = 1MHz

Total Capacitance, C_T (pF)

Reverse Voltage, V_R (V)

Forward Voltage Characteristics

Forward Current, I_F (mA)

Ta = 125
Ta = 75
Ta = 25
Ta = -25

Forward Voltage, V_F (V)

Forward Current Derating Curve

Average Rectified Forward Current, I_{OUT} (%)

Ambient Temperature, Ta ( )

Reverse Voltage Characteristics

Reverse Current, I_R (μA)

Ta = 125
Ta = 75
Ta = 25
Ta = -25

Reverse Voltage, V_R (V)